



IRU

PATENT  
Customer No. 22,852  
Attorney Docket No. 02887.0261

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
)  
Tomohiro SAITO ) Group Art Unit: 2823  
)  
Serial No.: 10/730,903 ) Examiner: William M. Brewster  
)  
Filed: December 10, 2003 ) Confirmation No.: 5163  
)  
For: SEMICONDUCTOR DEVICE AND )  
METHOD OF MANUFACTURING )  
THE SAME )  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**RESPONSE TO RESTRICTION REQUIREMENT**

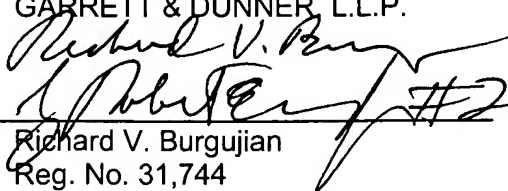
In a restriction requirement mailed June 22, 2005, the period for response to which extends through July 22, 2005, the Examiner required restriction under 35 U.S.C. § 121 between Group I, claims 1-12, characterized by the Examiner as being drawn to a method of selective etching of silicon material; and Group II, claims 13 and 14, characterized by the Examiner as being drawn to a field effect device with insulated electrode; Applicant provisionally elects to prosecute Group I, claims 1-12, without traverse.

Please grant any extensions of time required to enter this response and charge any additional required fees to our deposit account 06-0916.

Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW,  
GARRETT & DUNNER, L.L.P.

Dated: July 22, 2005

By:   
Richard V. Burgujian  
Reg. No. 31,744

#27,432